

L-2L De-embedding Method with Double-T-type PAD Model for Millimeter-wave Amplifier Design

<u>Seitaro Kawai</u>, Korkut Kaan Tokgoz, Kenichi Okada, and Akira Matsuzawa Tokyo Institute of Technology, Japan



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- Background, Motivation
- L-2L De-embedding
- Conventional PAD models
- Proposed 3 parameters PAD model
 - Transmission Line
 - 1-stage Amplifier
- Conclusion





Motivation

60GHz Gbps wireless communication

IEEE 802.11ad specification ■ 57.24GHz – 65.88 GHz

2.16GHz/ch x 4ch
10.56Gbps/ch in 64QAM



64QAM x 4 channles x 8MIMO → 300Gbps







60GHz CMOS Transceiver SIRF

Data rate : 28Gbps



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W SIRF **Circuit Components in mmW**









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De-embedding



Measurement results include PAD, TL. These components should be removed. De-embedding is the first step. Affect to modeling of all components.



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Problems









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Problems



- Capacitance of PAD affects to impedance.
- Capacitance is because of top-metal to ground.
- → It should be constant in high frequency.









It is impossible to get 3 parameter from L-2L.

Assumption: $Z_{S2} = k \times Z_{S} (0 \le k \le 1)$

Set "k" to be the PAD capacitance constant. (In this time, k=0.4)





M SIRF **De-embedding Results of TL**







Simulation Comparison



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L-2L de-embedding based on 3-parameter PAD model is proposed.

- According to the characteristic impedance of TL, the TL is de-embedded correctly.
- Simulation and measurement results are matched well.
- \rightarrow An accurate model in mm-W is realized.







Thank you for your attention!



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